



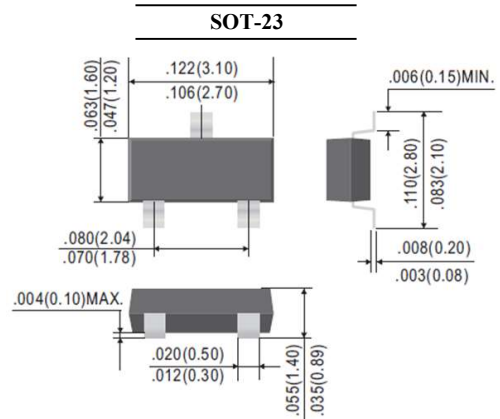
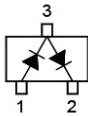
BAV199H

FAST SWITCHING DIODES

REVERSE VOLTAGE: 85 VOLTS
POWER DISSIPATION: 250 mWATTS

FEATURES

- Low leakage switching double diode
- For low leakage current applications
- Marking Code:PX
- Suffix "H" indicates Halogen-free parts, ex. BAV199H



Dimensions in inch and (millimeter)

Maximum Ratings@ $T_A=25\text{ }^\circ\text{C}$

Parameter	Symbol	Value	Unit
Peak Repetitive Reverse Voltage	V_{RRM}	85	V
Reverse Voltage	V_R	85	V
Forward Current	I_F	160	mA
Single Diode			
Double Diode		140	
Non-Repetitive Peak Forward Surge Current	I_{FSM}	at $t=1\mu\text{s}$	4
		at $t=1\text{ms}$	1
		at $t=1\text{s}$	0.5
Power Dissipation	P_D	250	mW
Thermal Resistance Junction to Ambient Air	$R_{\theta JA}$	500	$^\circ\text{C/W}$
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature Range	T_{STG}	-55 to +150	$^\circ\text{C}$

Electrical Characteristics@ $T_A=25\text{ }^\circ\text{C}$

Parameter	Conditions	Symbol	Min.	Typ.	Max.	Unit
Reverse Breakdown Voltage	$I_R=100\mu\text{A}$	$V_{(BR)R}$	85	-	-	V
Forward Voltage	$I_F=1\text{mA}$	V_F	-	-	900	mV
	$I_F=10\text{mA}$		-	-	1000	
	$I_F=50\text{mA}$		-	-	1100	
	$I_F=150\text{mA}$		-	-	1250	
Reverse current	$V_R=75\text{V}, T_J=25^\circ\text{C}$	I_R	-	-	5	nA
	$V_R=75\text{V}, T_J=125^\circ\text{C}$		-	-	80	
Typical Junction Measured at Capacitance	$V_R=0, f=1\text{MHz}$	C_J	-	2	-	pF
Reverse Recovery Time	$I_F=I_R=10\text{mA},$ $I_{rr}=0.1\times I_R, R_L=100\Omega$	t_{rr}	-	-	3	μs



BAV199H

FAST SWITCHING DIODES

RATINGS AND CHARACTERISTIC CURVES

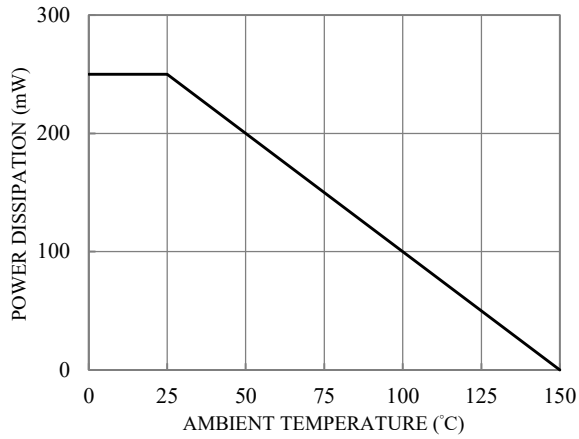


Fig.1-POWER DERATING CURVE

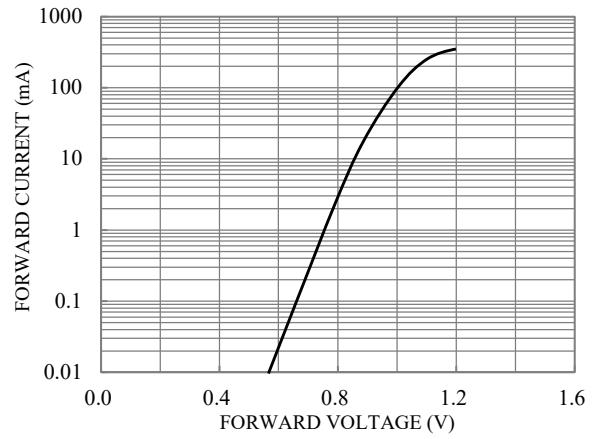


Fig.2-TYPICAL FORWARD CHARACTERISTICS

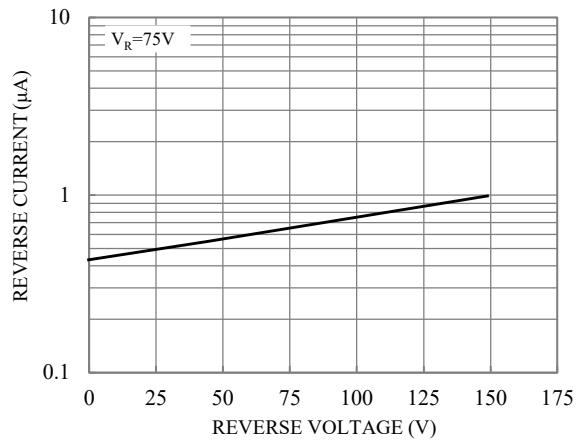


Fig.3-TYPICAL REVERSE CHARACTERISTICS

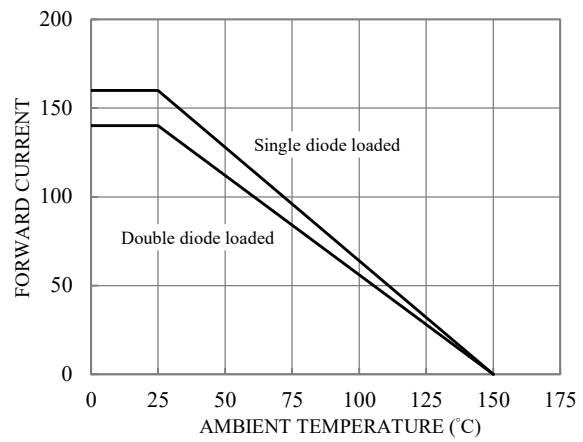


Fig.4-CURRENT DERATING CURVE